PROCESS CPD17

Ultra Fast Rectifier

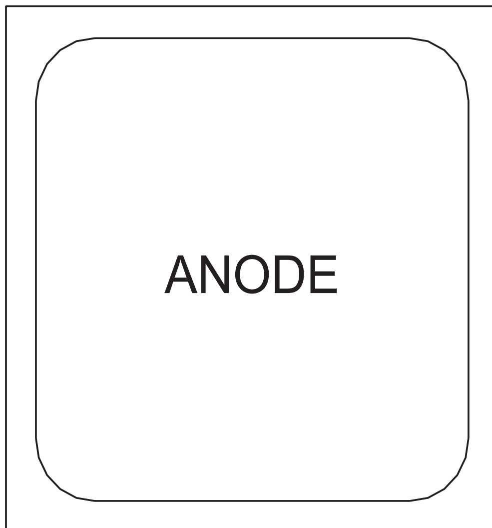
3 Amp Glass Passivated Rectifier Chip

Central™ Semiconductor Corp.

PROCESS DETAILS

Process	GLASS PASSIVATED MESA
Die Size	87 x 87 MILS
Die Thickness	12.2 MILS
Anode Bonding Pad Area	69.5 x 69.5 MILS
Top Side Metalization	Au - 5,000Å
Back Side Metalization	Au - 2,000Å

GEOMETRY



BACKSIDE CATHODE R0

GROSS DIE PER 4 INCH WAFER
1,490

PRINCIPAL DEVICE TYPES
1N5802 thru 1N5806
UES1101 thru UES1106
CMR3U-01 Series

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

R2 (19-September 2003)

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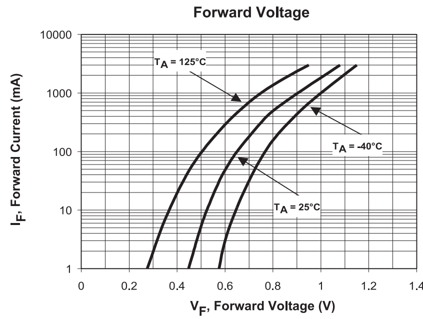
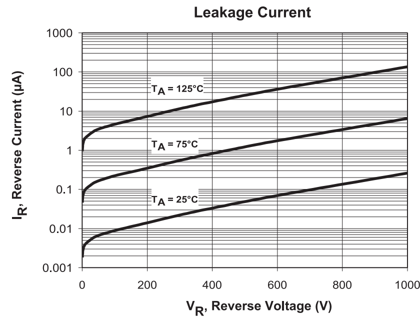
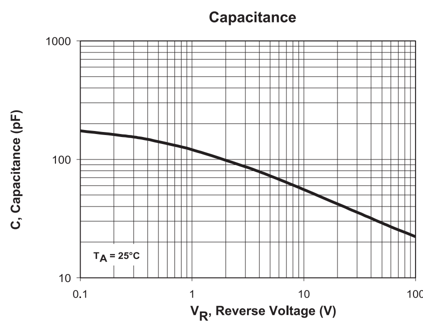
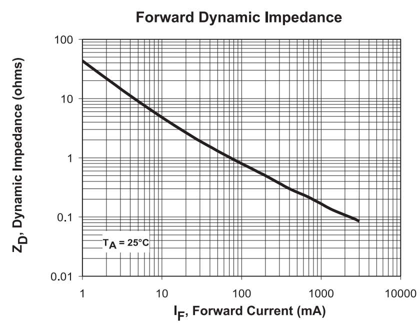
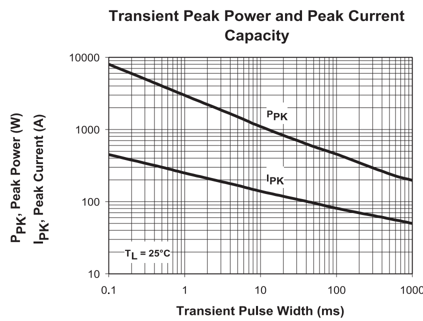
Typical Electrical Characteristics

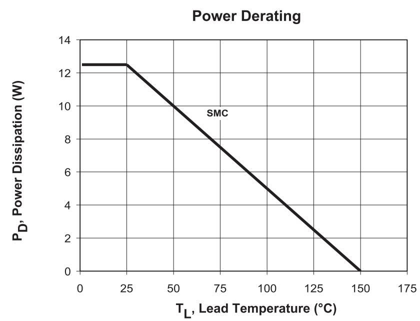












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